Switch-mode Power Rectifiers

MBR5H100MFS, NRVB5H100MFS

These state−of−the−art devices have the following features:

Features

- Low Power Loss / High Efficiency
- New Package Provides Capability of Inspection and Probe After Board Mounting
- Guardring for Stress Protection
- Low Forward Voltage Drop
- 175°C Operating Junction Temperature
- NRVB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These are Pb−Free Devices

Mechanical Characteristics:

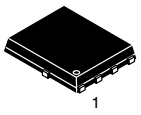
- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94−0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	100	V
Average Rectified Forward Current (Rated V_R, T_C = 150°C)	$I_{F(AV)}$	5	A
Peak Repetitive Forward Current, (Rated V_R, Square Wave, 20 kHz, T_C = 150°C)	I_{FRM}	10	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	200	A
Storage Temperature Range	T_{stg}	−65 to +175	°C
Operating Junction Temperature	T_J	−55 to +175	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs
Unclamped Inductive Switching Energy (10 mH Inductor, Non−repetitive)	E_{AS}	100	mJ
ESD Rating (Human Body Model)		3B	
ESD Rating (Machine Model)		C	

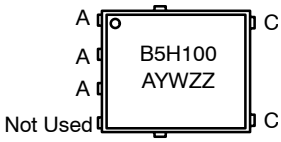
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

SCHOTTKY BARRIER RECTIFIERS 5 AMPERES 100 VOLTS



SO−8 FLAT LEAD CASE 488AA STYLE 2

MARKING DIAGRAM



B5H100 = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
MBR5H100MFST1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel
NRVB5H100MFST3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel

DISCONTINUED (Note 1)

MBR5H100MFST3G	SO−8 FL (Pb−Free)	5000 / Tape & Reel
NRVB5H100MFST1G	SO−8 FL (Pb−Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

1. **DISCONTINUED:** These devices are not recommended for new design. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction−to−Case, Steady State (Assumes 600 mm^2 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JC}$	−	2.4	°C/W

ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) (i_F = 5 Amps, T_J = 125°C) (i_F = 5 Amps, T_J = 25°C)	v_F	 0.56 0.6	 0.6 0.73	V
Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T_J = 125°C) (Rated dc Voltage, T_J = 25°C)	i_R	 3 0.003	 13 0.1	mA

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

TYPICAL CHARACTERISTICS

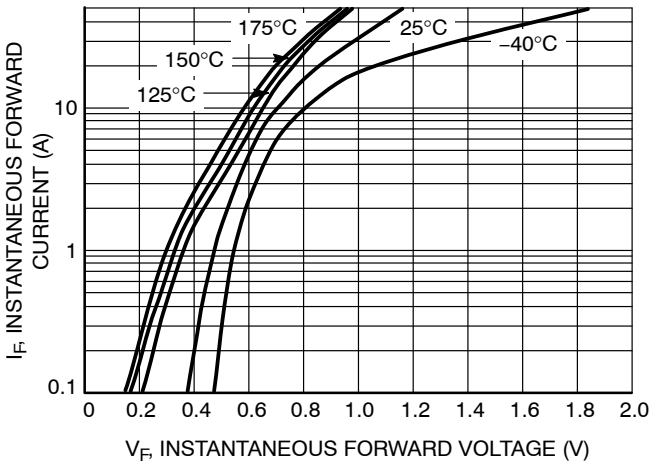


Figure 1. Typical Instantaneous Forward Characteristics

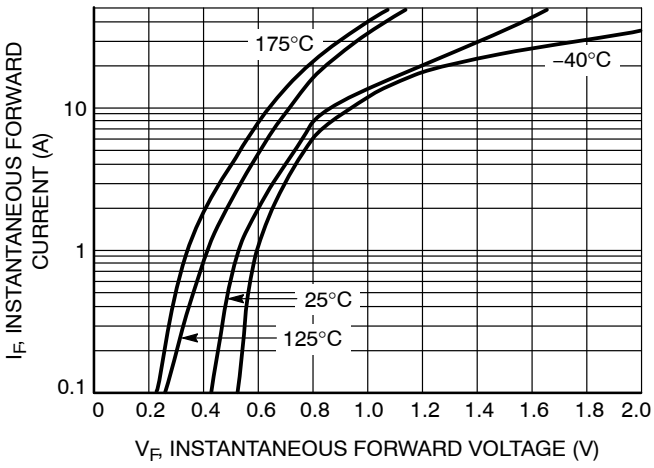


Figure 2. Maximum Instantaneous Forward Characteristics

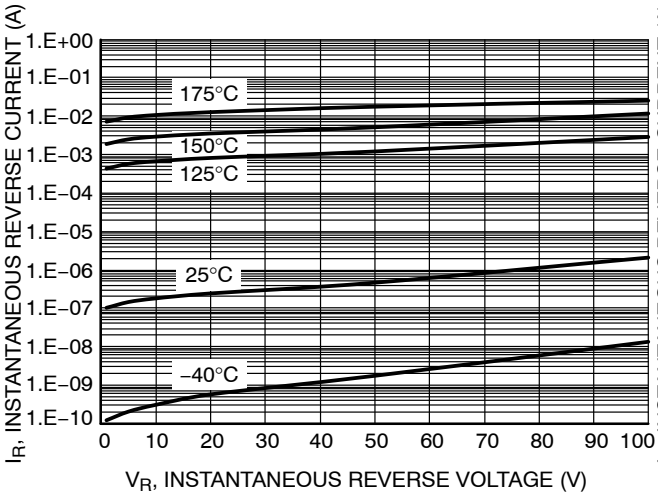


Figure 3. Typical Reverse Current Characteristics

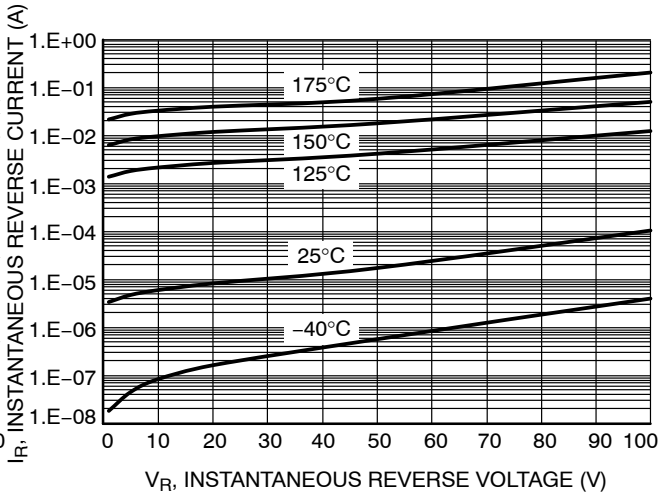


Figure 4. Maximum Reverse Current Characteristics

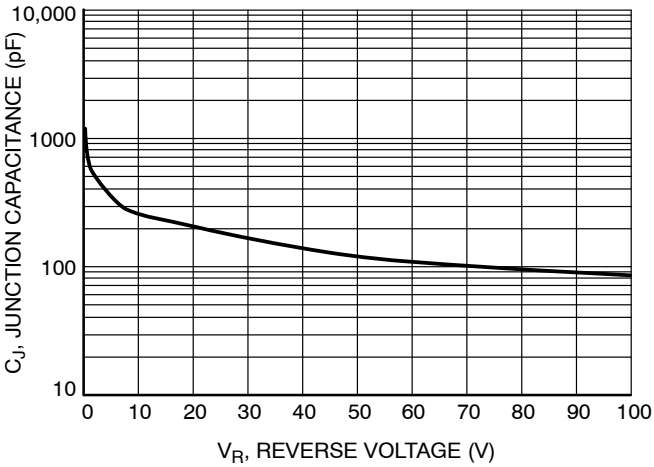


Figure 5. Typical Junction Capacitance

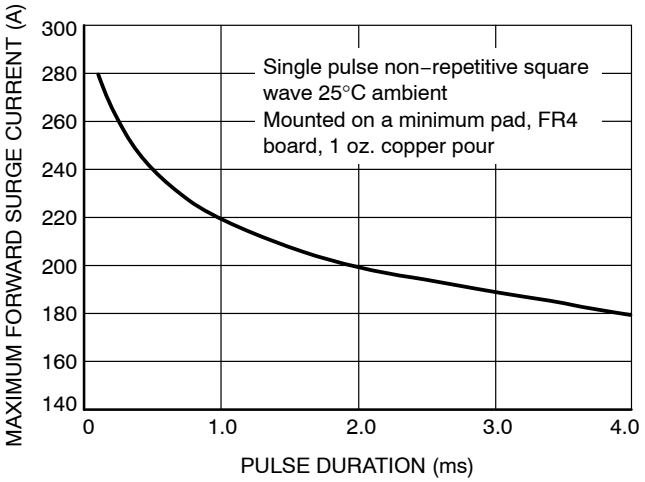


Figure 6. Forward Surge Safe Operating Area

TYPICAL CHARACTERISTICS

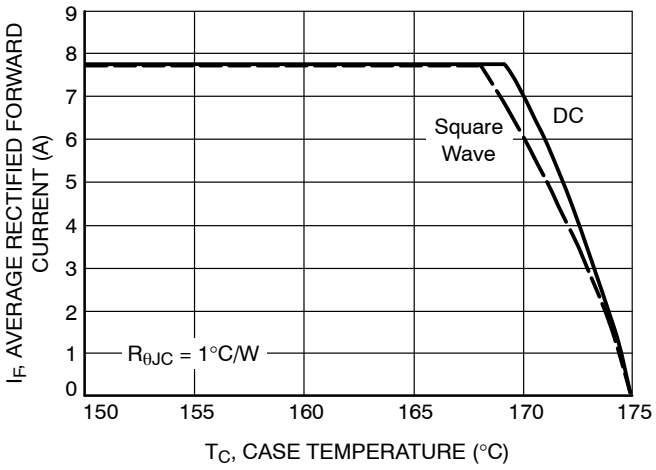


Figure 7. Forward Current Derating Over Case Temperature

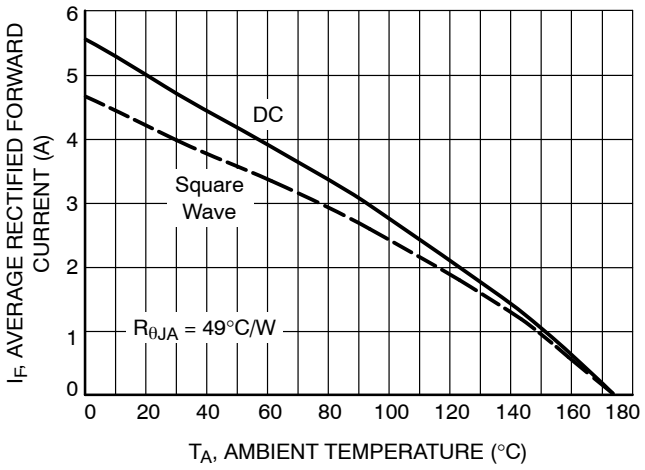


Figure 8. Forward Current Derating Over Ambient Temperature

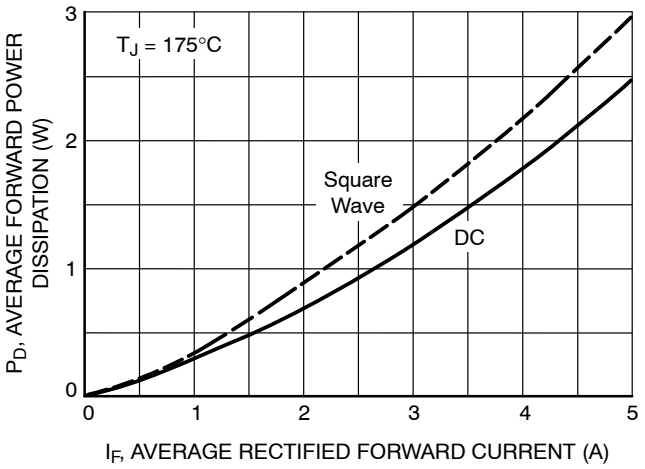


Figure 9. Maximum Forward Power Dissipation

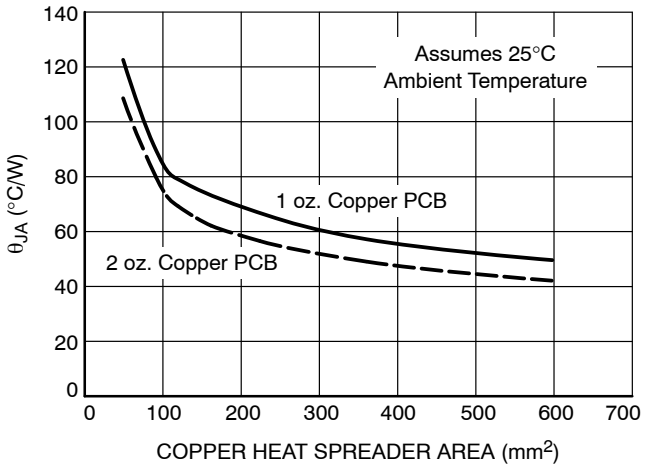


Figure 10. Steady State Junction to Ambient Thermal Resistance

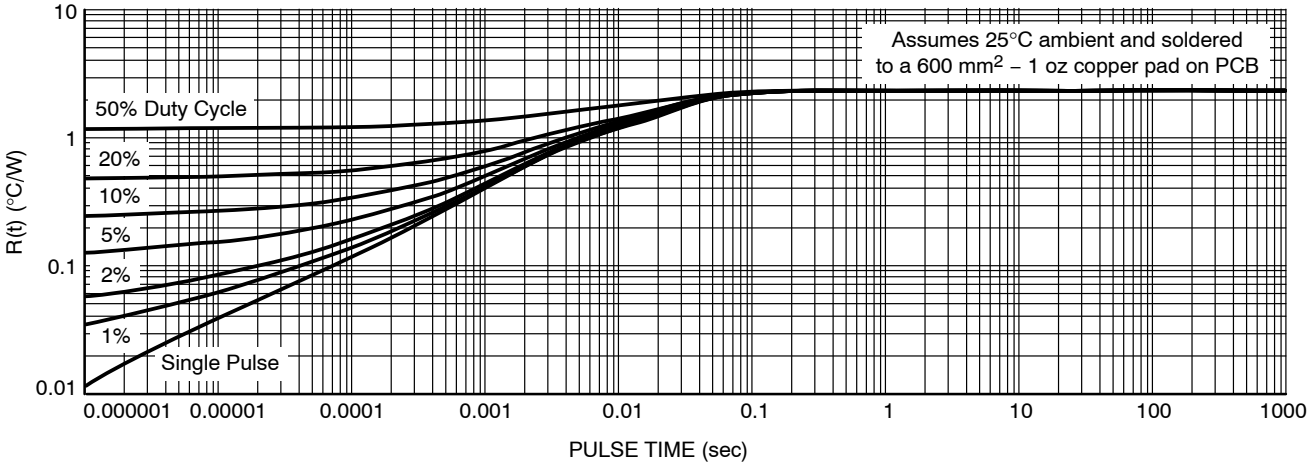
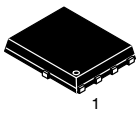


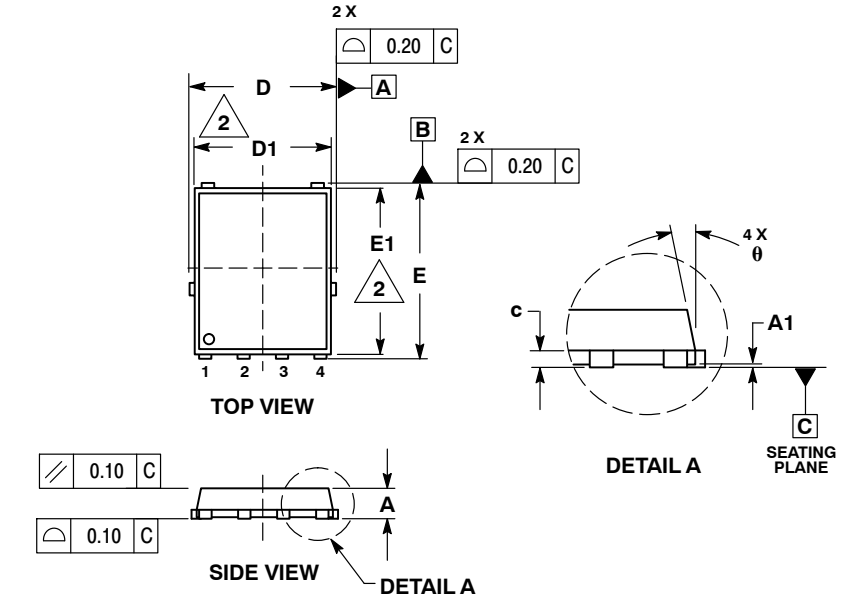
Figure 11. Transient Thermal Response, Junction to Case



SCALE 2:1

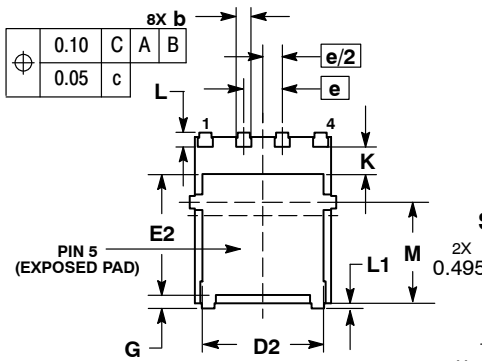
DFN5 5x6, 1.27P
(SO−8FL)
CASE 488AA
ISSUE N

DATE 25 JUN 2018

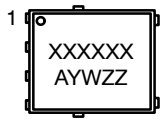


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	–––	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
θ	0 °	–––	12 °



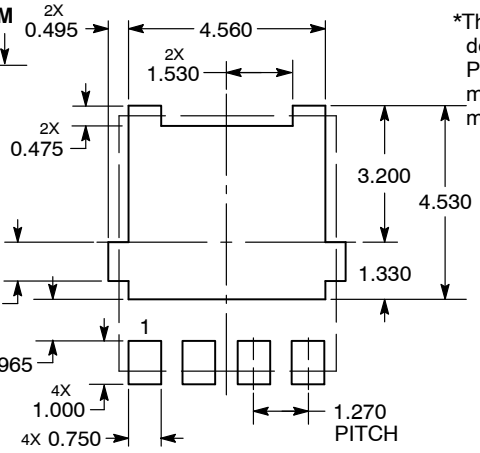
GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	**DFN5 5x6, 1.27P (SO−8FL)**		**PAGE 1 OF 1**

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